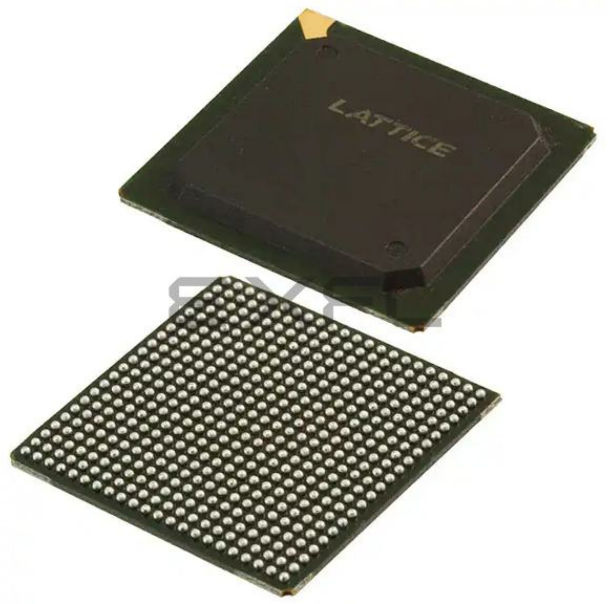

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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications,

Details	
Product Status	Active
Number of LABs/CLBs	858
Number of Logic Elements/Cells	6864
Total RAM Bits	245760
Number of I/O	334
Number of Gates	-
Voltage - Supply	1.14V ~ 1.26V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	484-BBGA
Supplier Device Package	484-FBGA (23x23)
Purchase URL	https://www.e-xfl.com/product-detail/lattice-semiconductor/lcmxo2-7000ze-1fg484c

The logic blocks, Programmable Functional Unit (PFU) and sysMEM EBR blocks, are arranged in a two-dimensional grid with rows and columns. Each row has either the logic blocks or the EBR blocks. The PIO cells are located at the periphery of the device, arranged in banks. The PFU contains the building blocks for logic, arithmetic, RAM, ROM, and register functions. The PIOs utilize a flexible I/O buffer referred to as a sysIO buffer that supports operation with a variety of interface standards. The blocks are connected with many vertical and horizontal routing channel resources. The place and route software tool automatically allocates these routing resources.

In the MachXO2 family, the number of sysIO banks varies by device. There are different types of I/O buffers on the different banks. Refer to the details in later sections of this document. The sysMEM EBRs are large, dedicated fast memory blocks; these blocks are found in MachXO2-640/U and larger devices. These blocks can be configured as RAM, ROM or FIFO. FIFO support includes dedicated FIFO pointer and flag "hard" control logic to minimize LUT usage.

The MachXO2 registers in PFU and sysI/O can be configured to be SET or RESET. After power up and device is configured, the device enters into user mode with these registers SET/RESET according to the configuration setting, allowing device entering to a known state for predictable system function.

The MachXO2 architecture also provides up to two sysCLOCK Phase Locked Loop (PLL) blocks on MachXO2-640U, MachXO2-1200/U and larger devices. These blocks are located at the ends of the on-chip Flash block. The PLLs have multiply, divide, and phase shifting capabilities that are used to manage the frequency and phase relationships of the clocks.

MachXO2 devices provide commonly used hardened functions such as SPI controller, I^2C controller and timer/counter. MachXO2-640/U and higher density devices also provide User Flash Memory (UFM). These hardened functions and the UFM interface to the core logic and routing through a WISHBONE interface. The UFM can also be accessed through the SPI, I^2C and JTAG ports.

Every device in the family has a JTAG port that supports programming and configuration of the device as well as access to the user logic. The MachXO2 devices are available for operation from 3.3 V, 2.5 V and 1.2 V power supplies, providing easy integration into the overall system.

PFU Blocks

The core of the MachXO2 device consists of PFU blocks, which can be programmed to perform logic, arithmetic, distributed RAM and distributed ROM functions. Each PFU block consists of four interconnected slices numbered 0 to 3 as shown in Figure 2-3. Each slice contains two LUTs and two registers. There are 53 inputs and 25 outputs associated with each PFU block.

This phase shift can be either programmed during configuration or can be adjusted dynamically. In dynamic mode, the PLL may lose lock after a phase adjustment on the output used as the feedback source and not relock until the t_{LOCK} parameter has been satisfied.

The MachXO2 also has a feature that allows the user to select between two different reference clock sources dynamically. This feature is implemented using the PLLREFCS primitive. The timing parameters for the PLL are shown in the sysCLOCK PLL Timing table.

The MachXO2 PLL contains a WISHBONE port feature that allows the PLL settings, including divider values, to be dynamically changed from the user logic. When using this feature the EFB block must also be instantiated in the design to allow access to the WISHBONE ports. Similar to the dynamic phase adjustment, when PLL settings are updated through the WISHBONE port the PLL may lose lock and not relock until the t_{LOCK} parameter has been satisfied. The timing parameters for the PLL are shown in the sysCLOCK PLL Timing table.

For more details on the PLL and the WISHBONE interface, see TN1199, MachXO2 sysCLOCK PLL Design and Usage Guide.

Figure 2-7. PLL Diagram

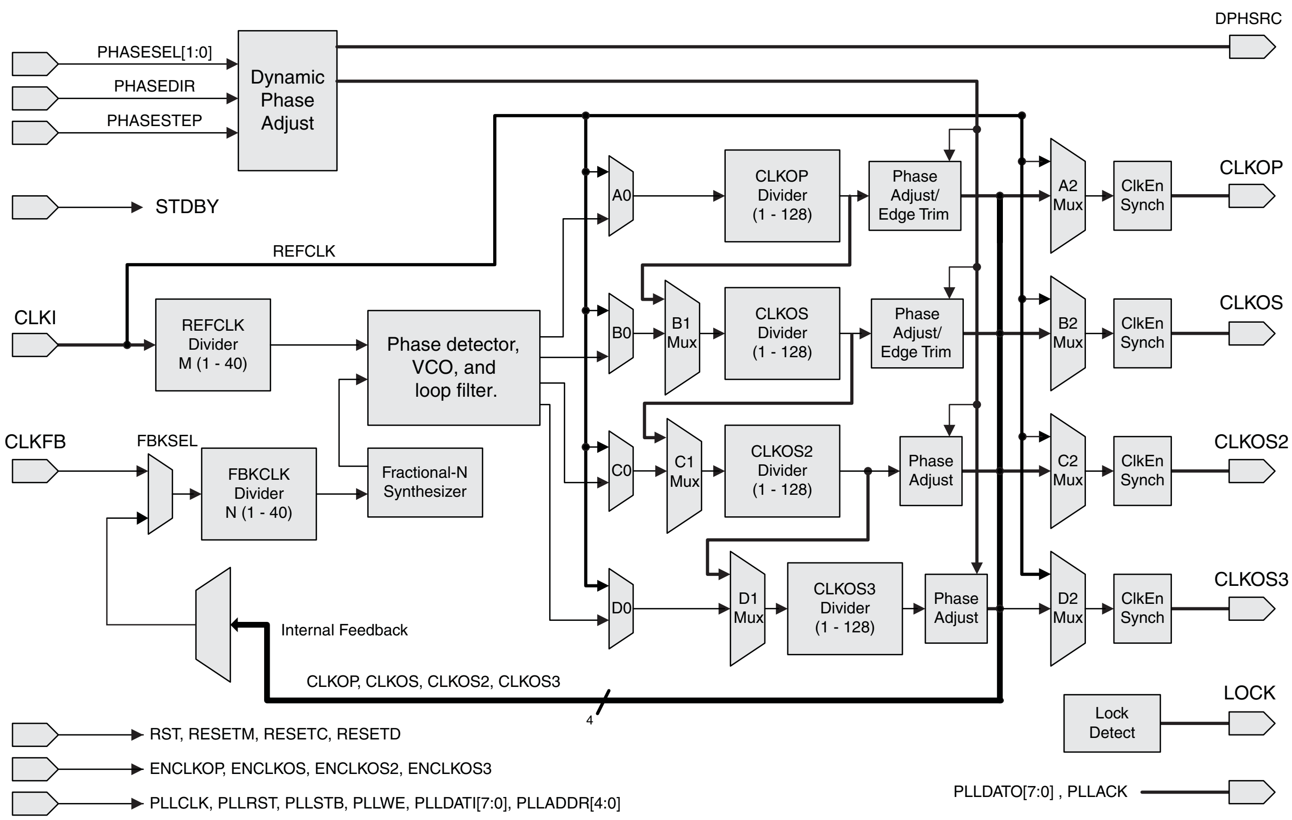
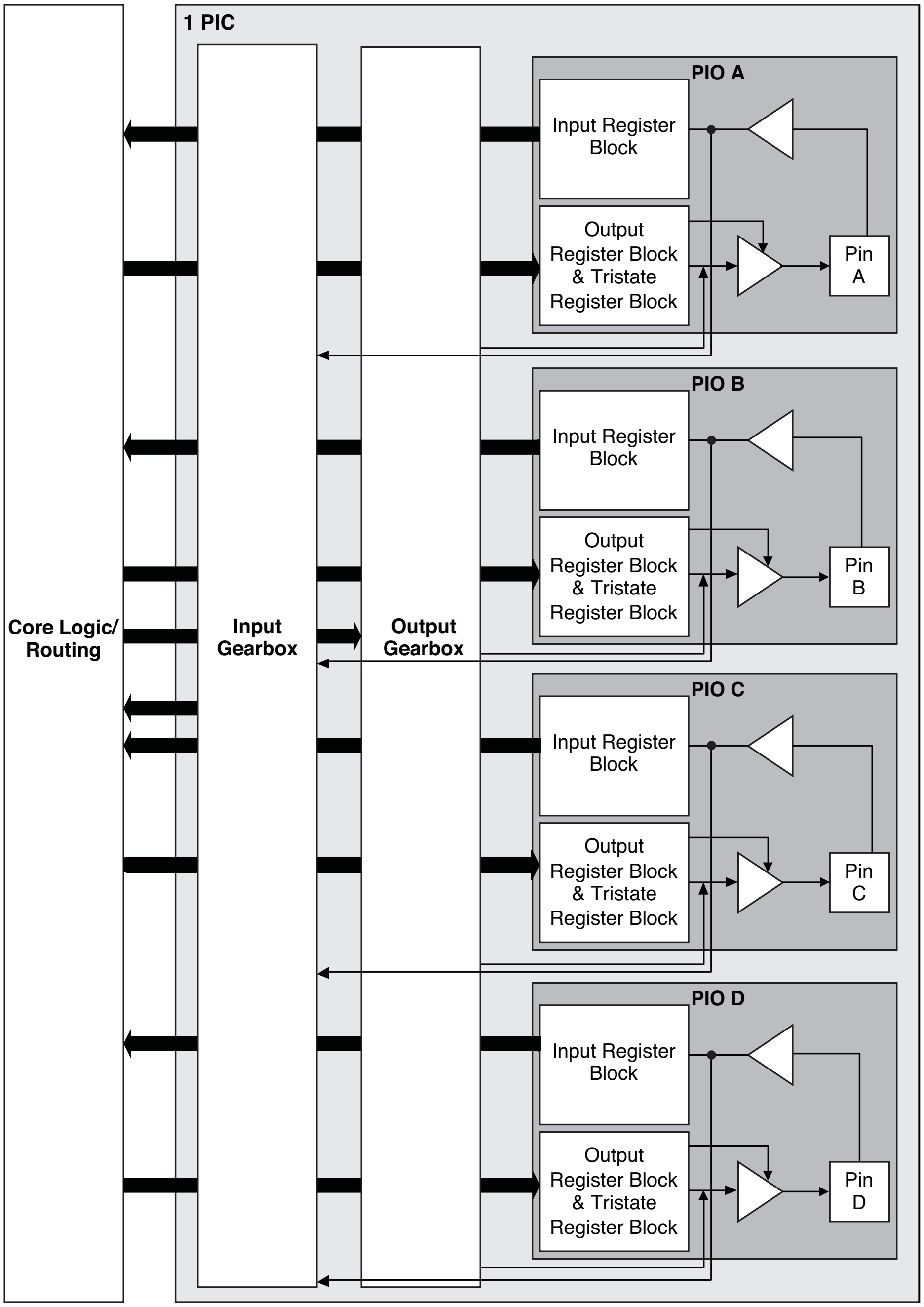


Table 2-4 provides signal descriptions of the PLL block.

Table 2-4. PLL Signal Descriptions

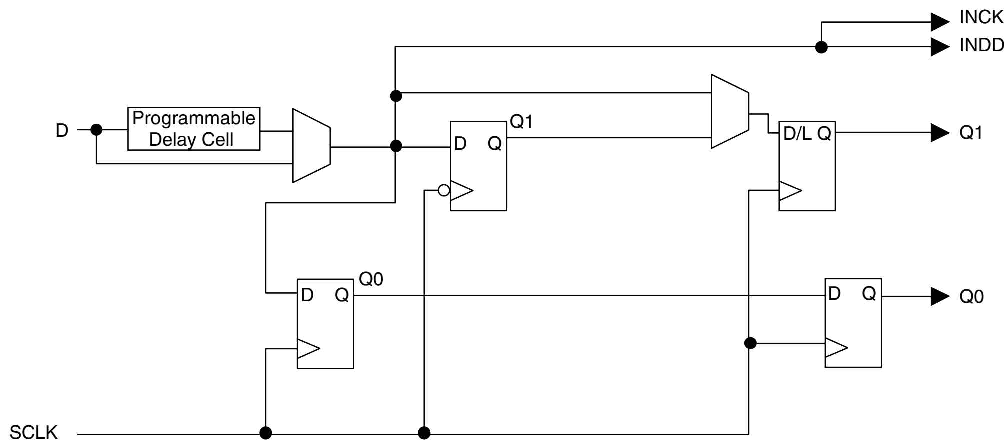
Port Name	I/O	Description
CLKI	I	Input clock to PLL
CLKFB	I	Feedback clock
PHASESEL[1:0]	I	Select which output is affected by Dynamic Phase adjustment ports
PHASEDIR	I	Dynamic Phase adjustment direction
PHASESTEP	I	Dynamic Phase step – toggle shifts VCO phase adjust by one step.

Figure 2-11. Group of Four Programmable I/O Cells



Notes:
1. Input gearbox is available only in PIC on the bottom edge of MachXO2-640U, MachXO2-1200/U and larger devices.
2. Output gearbox is available only in PIC on the top edge of MachXO2-640U, MachXO2-1200/U and larger devices.

Figure 2-12. MachXO2 Input Register Block Diagram (PIO on Left, Top and Bottom Edges)



Right Edge

The input register block on the right edge is a superset of the same block on the top, bottom, and left edges. In addition to the modes described above, the input register block on the right edge also supports DDR memory mode.

In DDR memory mode, two registers are used to sample the data on the positive and negative edges of the modified DQS (DQSR90) in the DDR Memory mode creating two data streams. Before entering the core, these two data streams are synchronized to the system clock to generate two data streams.

The signal DDRCLKPOL controls the polarity of the clock used in the synchronization registers. It ensures adequate timing when data is transferred to the system clock domain from the DQS domain. The DQSR90 and DDRCLKPOL signals are generated in the DQS read-write block.

Figure 2-13. MachXO2 Input Register Block Diagram (PIO on Right Edge)

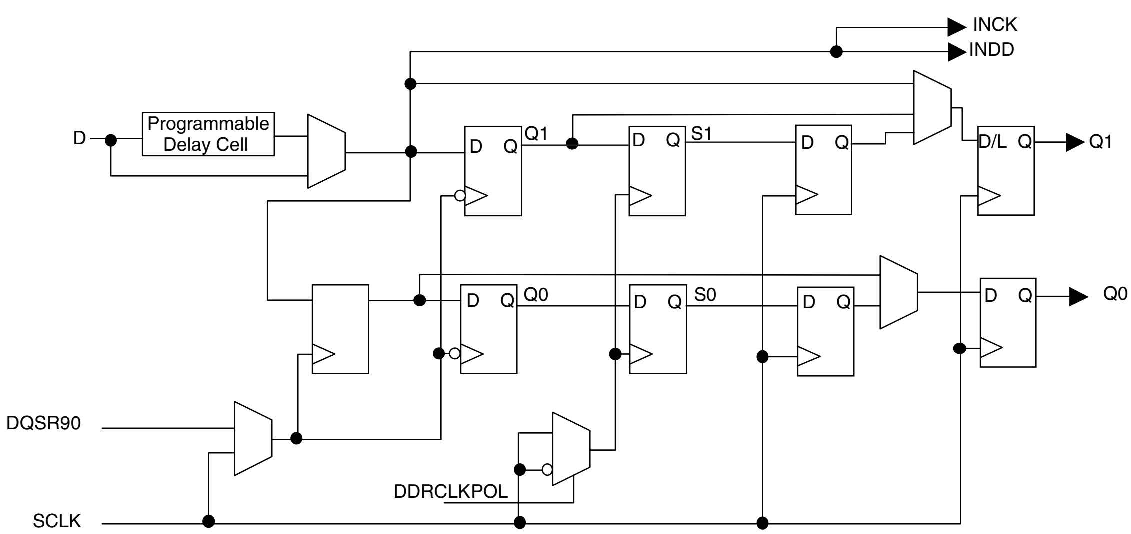
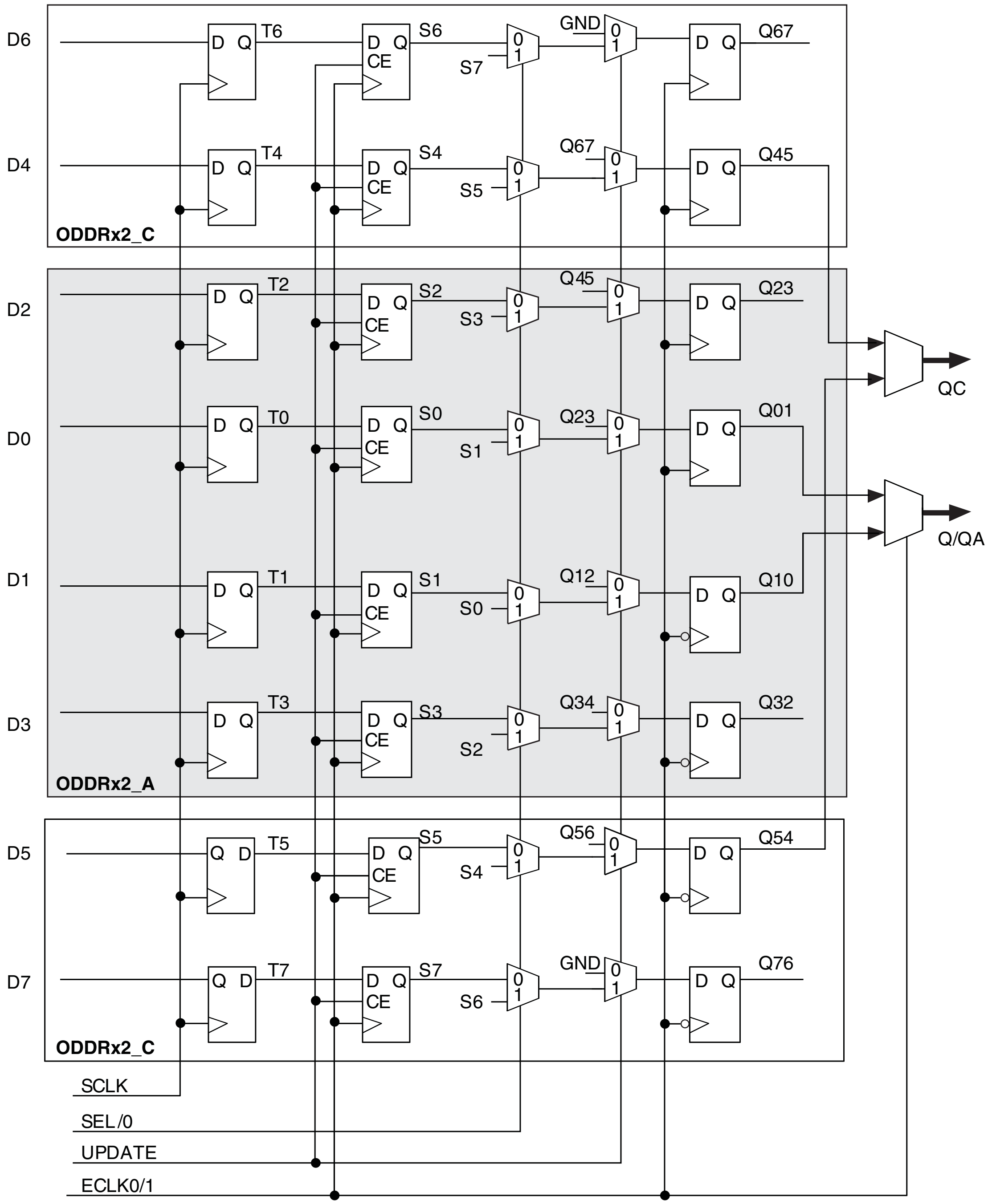


Figure 2-17. Output Gearbox



More information on the output gearbox is available in TN1203, Implementing High-Speed Interfaces with MachXO2 Devices.

DDR Memory Support

Certain PICs on the right edge of MachXO2-640U, MachXO2-1200/U and larger devices, have additional circuitry to allow the implementation of DDR memory interfaces. There are two groups of 14 or 12 PIOs each on the right edge with additional circuitry to implement DDR memory interfaces. This capability allows the implementation of up to 16-bit wide memory interfaces. One PIO from each group contains a control element, the DQS Read/Write Block, to facilitate the generation of clock and control signals (DQSR90, DQSW90, DDRCLKPOL and DATAVALID). These clock and control signals are distributed to the other PIO in the group through dedicated low skew routing.

DQS Read Write Block

Source synchronous interfaces generally require the input clock to be adjusted in order to correctly capture data at the input register. For most interfaces a PLL is used for this adjustment. However, in DDR memories the clock (referred to as DQS) is not free-running so this approach cannot be used. The DQS Read Write block provides the required clock alignment for DDR memory interfaces. DQSR90 and DQSW90 signals are generated by the DQS Read Write block from the DQS input.

In a typical DDR memory interface design, the phase relationship between the incoming delayed DQS strobe and the internal system clock (during the read cycle) is unknown. The MachXO2 family contains dedicated circuits to transfer data between these domains. To prevent set-up and hold violations, at the domain transfer between DQS (delayed) and the system clock, a clock polarity selector is used. This circuit changes the edge on which the data is registered in the synchronizing registers in the input register block. This requires evaluation at the start of each read cycle for the correct clock polarity. Prior to the read operation in DDR memories, DQS is in tri-state (pulled by termination). The DDR memory device drives DQS low at the start of the preamble state. A dedicated circuit in the DQS Read Write block detects the first DQS rising edge after the preamble state and generates the DDRCLKPOL signal. This signal is used to control the polarity of the clock to the synchronizing registers.

The temperature, voltage and process variations of the DQS delay block are compensated by a set of calibration signals (6-bit bus) from a DLL on the right edge of the device. The DLL loop is compensated for temperature, voltage and process variations by the system clock and feedback loop.

sysIO Buffer

Each I/O is associated with a flexible buffer referred to as a sysIO buffer. These buffers are arranged around the periphery of the device in groups referred to as banks. The sysIO buffers allow users to implement a wide variety of standards that are found in today's systems including LVCMOS, TTL, PCI, SSTL, HSTL, LVDS, BLVDS, MLVDS and LVPECL.

Each bank is capable of supporting multiple I/O standards. In the MachXO2 devices, single-ended output buffers, ratioed input buffers (LVTTL, LVCMOS and PCI), differential (LVDS) and referenced input buffers (SSTL and HSTL) are powered using I/O supply voltage (V_{CCIO}). Each sysIO bank has its own V_{CCIO}. In addition, each bank has a voltage reference, V_{REF}, which allows the use of referenced input buffers independent of the bank V_{CCIO}.

MachXO2-256 and MachXO2-640 devices contain single-ended ratioed input buffers and single-ended output buffers with complementary outputs on all the I/O banks. Note that the single-ended input buffers on these devices do not contain PCI clamps. In addition to the single-ended I/O buffers these two devices also have differential and referenced input buffers on all I/Os. The I/Os are arranged in pairs, the two pads in the pair are described as "T" and "C", where the true pad is associated with the positive side of the differential input buffer and the comp (complementary) pad is associated with the negative side of the differential input buffer.

There are some limitations on the use of the hardened user SPI. These are defined in the following technical notes:

- TN1087, Minimizing System Interruption During Configuration Using TransFR Technology (Appendix B)
- TN1205, Using User Flash Memory and Hardened Control Functions in MachXO2 Devices

Figure 2-22. SPI Core Block Diagram

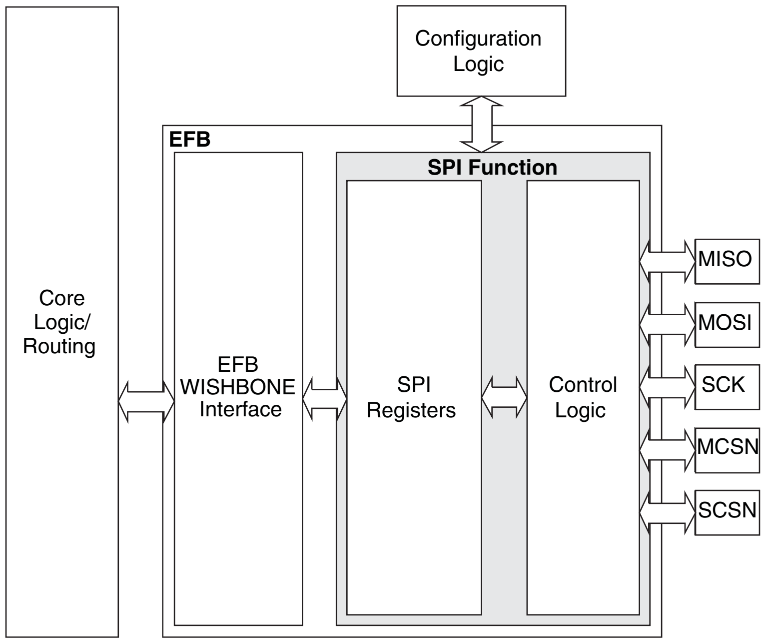


Table 2-16 describes the signals interfacing with the SPI cores.

Table 2-16. SPI Core Signal Description

Signal Name	I/O	Master/Slave	Description
spi_csn[0]	O	Master	SPI master chip-select output
spi_csn[1..7]	O	Master	Additional SPI chip-select outputs (total up to eight slaves)
spi_scsn	I	Slave	SPI slave chip-select input
spi_irq	O	Master/Slave	Interrupt request
spi_clk	I/O	Master/Slave	SPI clock. Output in master mode. Input in slave mode.
spi_miso	I/O	Master/Slave	SPI data. Input in master mode. Output in slave mode.
spi_mosi	I/O	Master/Slave	SPI data. Output in master mode. Input in slave mode.
ufm_sn	I	Slave	Configuration Slave Chip Select (active low), dedicated for selecting the User Flash Memory (UFM).
cfg_stdby	O	Master/Slave	Stand-by signal – To be connected only to the power module of the MachXO2 device. The signal is enabled only if the “Wakeup Enable” feature has been set within the EFB GUI, SPI Tab.
cfg_wake	O	Master/Slave	Wake-up signal – To be connected only to the power module of the MachXO2 device. The signal is enabled only if the “Wakeup Enable” feature has been set within the EFB GUI, SPI Tab.

Configuration and Testing

This section describes the configuration and testing features of the MachXO2 family.

IEEE 1149.1-Compliant Boundary Scan Testability

All MachXO2 devices have boundary scan cells that are accessed through an IEEE 1149.1 compliant test access port (TAP). This allows functional testing of the circuit board, on which the device is mounted, through a serial scan path that can access all critical logic nodes. Internal registers are linked internally, allowing test data to be shifted in and loaded directly onto test nodes, or test data to be captured and shifted out for verification. The test access port consists of dedicated I/Os: TDI, TDO, TCK and TMS. The test access port shares its power supply with V_{CCIO} Bank 0 and can operate with LVCMOS3.3, 2.5, 1.8, 1.5, and 1.2 standards.

For more details on boundary scan test, see AN8066, Boundary Scan Testability with Lattice sysIO Capability and TN1087, Minimizing System Interruption During Configuration Using TransFR Technology.

Device Configuration

All MachXO2 devices contain two ports that can be used for device configuration. The Test Access Port (TAP), which supports bit-wide configuration and the sysCONFIG port which supports serial configuration through I^2C or SPI. The TAP supports both the IEEE Standard 1149.1 Boundary Scan specification and the IEEE Standard 1532 In-System Configuration specification. There are various ways to configure a MachXO2 device:

1. Internal Flash Download
2. JTAG
3. Standard Serial Peripheral Interface (Master SPI mode) – interface to boot PROM memory
4. System microprocessor to drive a serial slave SPI port (SSPI mode)
5. Standard I^2C Interface to system microprocessor

Upon power-up, the configuration SRAM is ready to be configured using the selected sysCONFIG port. Once a configuration port is selected, it will remain active throughout that configuration cycle. The IEEE 1149.1 port can be activated any time after power-up by sending the appropriate command through the TAP port. Optionally the device can run a CRC check upon entering the user mode. This will ensure that the device was configured correctly.

The sysCONFIG port has 10 dual-function pins which can be used as general purpose I/Os if they are not required for configuration. See TN1204, MachXO2 Programming and Configuration Usage Guide for more information about using the dual-use pins as general purpose I/Os.

Lattice design software uses proprietary compression technology to compress bit-streams for use in MachXO2 devices. Use of this technology allows Lattice to provide a lower cost solution. In the unlikely event that this technology is unable to compress bitstreams to fit into the amount of on-chip Flash memory, there are a variety of techniques that can be utilized to allow the bitstream to fit in the on-chip Flash memory. For more details, refer to TN1204, MachXO2 Programming and Configuration Usage Guide.

The Test Access Port (TAP) has five dual purpose pins (TDI, TDO, TMS, TCK and JTAGENB). These pins are dual function pins - TDI, TDO, TMS and TCK can be used as general purpose I/O if desired. For more details, refer to TN1204, MachXO2 Programming and Configuration Usage Guide.

TransFR (Transparent Field Reconfiguration)

TransFR is a unique Lattice technology that allows users to update their logic in the field without interrupting system operation using a simple push-button solution. For more details refer to TN1087, Minimizing System Interruption During Configuration Using TransFR Technology for details.

Power-On-Reset Voltage Levels[1, 2, 3, 4, 5]

Symbol	Parameter	Min.	Typ.	Max.	Units
V_{PORUP}	Power-On-Reset ramp up trip point (band gap based circuit monitoring V_{CCINT} and V_{CCIO0})	0.9	—	1.06	V
$V_{PORUPEXT}$	Power-On-Reset ramp up trip point (band gap based circuit monitoring external V_{CC} power supply)	1.5	—	2.1	V
$V_{PORDNBG}$	Power-On-Reset ramp down trip point (band gap based circuit monitoring V_{CCINT})	0.75	—	0.93	V
$V_{PORDNBGEXT}$	Power-On-Reset ramp down trip point (band gap based circuit monitoring V_{CC})	0.98	—	1.33	V
$V_{PORDNSRAM}$	Power-On-Reset ramp down trip point (SRAM based circuit monitoring V_{CCINT})	—	0.6	—	V
$V_{PORDNSRAMEXT}$	Power-On-Reset ramp down trip point (SRAM based circuit monitoring V_{CC})	—	0.96	—	V

1. These POR trip points are only provided for guidance. Device operation is only characterized for power supply voltages specified under recommended operating conditions.
2. For devices without voltage regulators V_{CCINT} is the same as the V_{CC} supply voltage. For devices with voltage regulators, V_{CCINT} is regulated from the V_{CC} supply voltage.
3. Note that V_{PORUP} (min.) and $V_{PORDNBG}$ (max.) are in different process corners. For any given process corner $V_{PORDNBG}$ (max.) is always 12.0 mV below V_{PORUP} (min.).
4. $V_{PORUPEXT}$ is for HC devices only. In these devices a separate POR circuit monitors the external V_{CC} power supply.
5. V_{CCIO0} does not have a Power-On-Reset ramp down trip point. V_{CCIO0} must remain within the Recommended Operating Conditions to ensure proper operation.

Programming/Erase Specifications

Symbol	Parameter	Min.	Max.[1]	Units
$N_{PROGCYC}$	Flash Programming cycles per $t_{RETENTION}$	—	10,000	Cycles
	Flash functional programming cycles	—	100,000	
$t_{RETENTION}$	Data retention at 100 °C junction temperature	10	—	Years
	Data retention at 85 °C junction temperature	20	—	

1. Maximum Flash memory reads are limited to 7.5E13 cycles over the lifetime of the product.

Hot Socketing Specifications[1, 2, 3]

Symbol	Parameter	Condition	Max.	Units
I_{DK}	Input or I/O leakage Current	$0 < V_{IN} < V_{IH}$ (MAX)	+/–1000	µA

1. Insensitive to sequence of V_{CC} and V_{CCIO}. However, assumes monotonic rise/fall rates for V_{CC} and V_{CCIO}.
2. $0 < V_{CC} < V_{CC}$ (MAX), $0 < V_{CCIO} < V_{CCIO}$ (MAX).
3. I_{DK} is additive to I_{PU}, I_{PD} or I_{BH}.

ESD Performance

Please refer to the MachXO2 Product Family Qualification Summary for complete qualification data, including ESD performance.

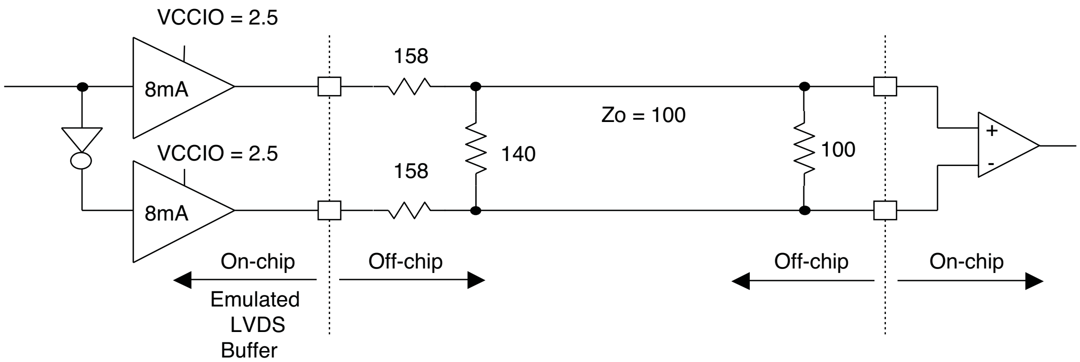
sysIO Single-Ended DC Electrical Characteristics[1, 2]

Input/Output Standard	V_{IL} Min. (V)[3]	V_{IL} Max. (V)	V_{IH} Min. (V)	V_{IH} Max. (V)	V_{OL} Max. (V)	V_{OH} Min. (V)	I_{OL} Max.[4] (mA)	I_{OH} Max.[4] (mA)
LVCMOS 3.3 LVTTL	-0.3	0.8	2.0	3.6	0.4	V_{CCIO} – 0.4	4	–4
							8	–8
							12	–12
							16	–16
							24	–24
					0.2	V_{CCIO} – 0.2	0.1	–0.1
LVCMOS 2.5	–0.3	0.7	1.7	3.6	0.4	V_{CCIO} – 0.4	4	–4
							8	–8
							12	–12
							16	–16
					0.2	V_{CCIO} – 0.2	0.1	–0.1
LVCMOS 1.8	–0.3	0.35V_{CCIO}	0.65V_{CCIO}	3.6	0.4	V_{CCIO} – 0.4	4	–4
							8	–8
							12	–12
					0.2	V_{CCIO} – 0.2	0.1	–0.1
LVCMOS 1.5	–0.3	0.35V_{CCIO}	0.65V_{CCIO}	3.6	0.4	V_{CCIO} – 0.4	4	–4
							8	–8
					0.2	V_{CCIO} – 0.2	0.1	–0.1
LVCMOS 1.2	–0.3	0.35V_{CCIO}	0.65V_{CCIO}	3.6	0.4	V_{CCIO} – 0.4	4	–2
							8	–6
					0.2	V_{CCIO} – 0.2	0.1	–0.1
PCI	–0.3	0.3V_{CCIO}	0.5V_{CCIO}	3.6	0.1V_{CCIO}	0.9V_{CCIO}	1.5	–0.5
SSTL25 Class I	–0.3	V_{REF} – 0.18	V_{REF} + 0.18	3.6	0.54	V_{CCIO} - 0.62	8	8
SSTL25 Class II	–0.3	V_{REF} – 0.18	V_{REF} + 0.18	3.6	NA	NA	NA	NA
SSTL18 Class I	–0.3	V_{REF} – 0.125	V_{REF} + 0.125	3.6	0.40	V_{CCIO} - 0.40	8	8
SSTL18 Class II	–0.3	V_{REF} – 0.125	V_{REF} + 0.125	3.6	NA	NA	NA	NA
HSTL18 Class I	–0.3	V_{REF} – 0.1	V_{REF} + 0.1	3.6	0.40	V_{CCIO} - 0.40	8	8
HSTL18 Class II	–0.3	V_{REF} – 0.1	V_{REF} + 0.1	3.6	NA	NA	NA	NA
LVCMOS25R33	–0.3	V_{REF} – 0.1	V_{REF} + 0.1	3.6	NA	NA	NA	NA
LVCMOS18R33	–0.3	V_{REF} – 0.1	V_{REF} + 0.1	3.6	NA	NA	NA	NA
LVCMOS18R25	–0.3	V_{REF} – 0.1	V_{REF} + 0.1	3.6	NA	NA	NA	NA
LVCMOS15R33	–0.3	V_{REF} – 0.1	V_{REF} + 0.1	3.6	NA	NA	NA	NA
LVCMOS15R25	–0.3	V_{REF} – 0.1	V_{REF} + 0.1	3.6	NA	NA	NA	NA
LVCMOS12R33	–0.3	V_{REF} – 0.1	V_{REF} + 0.1	3.6	0.40	NA Open Drain	24, 16, 12, 8, 4	NA Open Drain
LVCMOS12R25	–0.3	V_{REF} – 0.1	V_{REF} + 0.1	3.6	0.40	NA Open Drain	16, 12, 8, 4	NA Open Drain
LVCMOS10R33	–0.3	V_{REF} – 0.1	V_{REF} + 0.1	3.6	0.40	NA Open Drain	24, 16, 12, 8, 4	NA Open Drain

LVDS Emulation

MachXO2 devices can support LVDS outputs via emulation (LVDS25E). The output is emulated using complementary LVCMOS outputs in conjunction with resistors across the driver outputs on all devices. The scheme shown in Figure 3-1 is one possible solution for LVDS standard implementation. Resistor values in Figure 3-1 are industry standard values for 1% resistors.

Figure 3-1. LVDS Using External Resistors (LVDS25E)



Note: All resistors are ±1%.

Table 3-1. LVDS25E DC Conditions

Over Recommended Operating Conditions

Parameter	Description	Typ.	Units
Z_{OUT}	Output impedance	20	Ohms
R_S	Driver series resistor	158	Ohms
R_P	Driver parallel resistor	140	Ohms
R_T	Receiver termination	100	Ohms
V_{OH}	Output high voltage	1.43	V
V_{OL}	Output low voltage	1.07	V
V_{OD}	Output differential voltage	0.35	V
V_{CM}	Output common mode voltage	1.25	V
Z_{BACK}	Back impedance	100.5	Ohms
I_{DC}	DC output current	6.03	mA

RSDS

The MachXO2 family supports the differential RSDS standard. The output standard is emulated using complementary LVCMOS outputs in conjunction with resistors across the driver outputs on all the devices. The RSDS input standard is supported by the LVDS differential input buffer. The scheme shown in Figure 3-4 is one possible solution for RSDS standard implementation. Use LVDS25E mode with suggested resistors for RSDS operation. Resistor values in Figure 3-4 are industry standard values for 1% resistors.

Figure 3-4. RSDS (Reduced Swing Differential Standard)

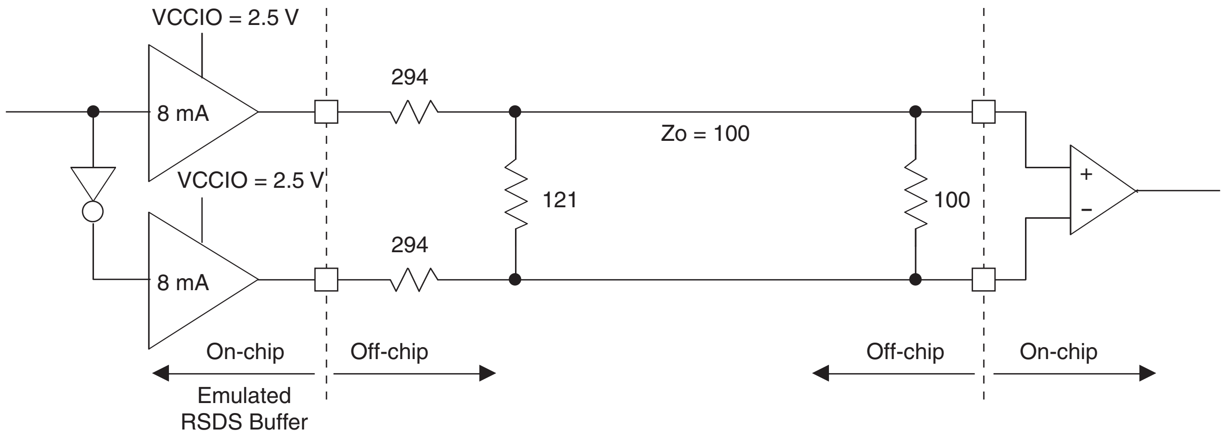


Table 3-4. RSDS DC Conditions

Parameter	Description	Typical	Units
Z_{OUT}	Output impedance	20	Ohms
R_S	Driver series resistor	294	Ohms
R_P	Driver parallel resistor	121	Ohms
R_T	Receiver termination	100	Ohms
V_{OH}	Output high voltage	1.35	V
V_{OL}	Output low voltage	1.15	V
V_{OD}	Output differential voltage	0.20	V
V_{CM}	Output common mode voltage	1.25	V
Z_{BACK}	Back impedance	101.5	Ohms
I_{DC}	DC output current	3.66	mA

Parameter	Description	Device	–6 Min.	–6 Max.	–5 Min.	–5 Max.	–4 Min.	–4 Max.	Units
Generic DDR4 Inputs with Clock and Data Aligned at Pin Using PCLK Pin for Clock Input – GDDRX4_RX.ECLK.Aligned[9, 12]									
t_{DVA}	Input Data Valid After ECLK	MachXO2-640U, MachXO2-1200/U and larger devices, bottom side only.[11]	—	0.290	—	0.320	—	0.345	UI
t_{DVE}	Input Data Hold After ECLK		0.739	—	0.699	—	0.703	—	UI
f_{DATA}	DDRX4 Serial Input Data Speed		—	756	—	630	—	524	Mbps
f_{DDRX4}	DDRX4 ECLK Frequency		—	378	—	315	—	262	MHz
f_{SCLK}	SCLK Frequency		—	95	—	79	—	66	MHz
Generic DDR4 Inputs with Clock and Data Centered at Pin Using PCLK Pin for Clock Input – GDDRX4_RX.ECLK.Centered[9, 12]									
t_{SU}	Input Data Setup Before ECLK	MachXO2-640U, MachXO2-1200/U and larger devices, bottom side only.[11]	0.233	—	0.219	—	0.198	—	ns
t_{HO}	Input Data Hold After ECLK		0.287	—	0.287	—	0.344	—	ns
f_{DATA}	DDRX4 Serial Input Data Speed		—	756	—	630	—	524	Mbps
f_{DDRX4}	DDRX4 ECLK Frequency		—	378	—	315	—	262	MHz
f_{SCLK}	SCLK Frequency		—	95	—	79	—	66	MHz
7:1 LVDS Inputs (GDDR71_RX.ECLK.7:1)[9, 12]									
t_{DVA}	Input Data Valid After ECLK	MachXO2-640U, MachXO2-1200/U and larger devices, bottom side only.[11]	—	0.290	—	0.320	—	0.345	UI
t_{DVE}	Input Data Hold After ECLK		0.739	—	0.699	—	0.703	—	UI
f_{DATA}	DDR71 Serial Input Data Speed		—	756	—	630	—	524	Mbps
f_{DDR71}	DDR71 ECLK Frequency		—	378	—	315	—	262	MHz
f_{CLKIN}	7:1 Input Clock Frequency (SCLK) (minimum limited by PLL)		—	108	—	90	—	75	MHz
Generic DDR Outputs with Clock and Data Aligned at Pin Using PCLK Pin for Clock Input – GDDRX1_TX.SCLK.Aligned[9, 12]									
t_{DIA}	Output Data Invalid After CLK Output	All MachXO2 devices, all sides.	—	0.520	—	0.550	—	0.580	ns
t_{DIB}	Output Data Invalid Before CLK Output		—	0.520	—	0.550	—	0.580	ns
f_{DATA}	DDRX1 Output Data Speed		—	300	—	250	—	208	Mbps
f_{DDRX1}	DDRX1 SCLK frequency		—	150	—	125	—	104	MHz
Generic DDR Outputs with Clock and Data Centered at Pin Using PCLK Pin for Clock Input – GDDRX1_TX.SCLK.Centered[9, 12]									
t_{DVB}	Output Data Valid Before CLK Output	All MachXO2 devices, all sides.	1.210	—	1.510	—	1.870	—	ns
t_{DVA}	Output Data Valid After CLK Output		1.210	—	1.510	—	1.870	—	ns
f_{DATA}	DDRX1 Output Data Speed		—	300	—	250	—	208	Mbps
f_{DDRX1}	DDRX1 SCLK Frequency (minimum limited by PLL)		—	150	—	125	—	104	MHz
Generic DDRX2 Outputs with Clock and Data Aligned at Pin Using PCLK Pin for Clock Input – GDDRX2_TX.ECLK.Aligned[9, 12]									
t_{DIA}	Output Data Invalid After CLK Output	MachXO2-640U, MachXO2-1200/U and larger devices, top side only.	—	0.200	—	0.215	—	0.230	ns
t_{DIB}	Output Data Invalid Before CLK Output		—	0.200	—	0.215	—	0.230	ns
f_{DATA}	DDRX2 Serial Output Data Speed		—	664	—	554	—	462	Mbps
f_{DDRX2}	DDRX2 ECLK frequency		—	332	—	277	—	231	MHz
f_{SCLK}	SCLK Frequency		—	166	—	139	—	116	MHz

MachXO2 External Switching Characteristics – ZE Devices[1, 2, 3, 4, 5, 6, 7]

Over Recommended Operating Conditions

Parameter	Description	Device	–3		–2		–1		Units
			Min.	Max.	Min.	Max.	Min.	Max.	
Clocks									
Primary Clocks									
f_{MAX_PRI}[8]	Frequency for Primary Clock Tree	All MachXO2 devices	—	150	—	125	—	104	MHz
t_{W_PRI}	Clock Pulse Width for Primary Clock	All MachXO2 devices	1.00	—	1.20	—	1.40	—	ns
t_{SKEW_PRI}	Primary Clock Skew Within a Device	MachXO2-256ZE	—	1250	—	1272	—	1296	ps
		MachXO2-640ZE	—	1161	—	1183	—	1206	ps
		MachXO2-1200ZE	—	1213	—	1267	—	1322	ps
		MachXO2-2000ZE	—	1204	—	1250	—	1296	ps
		MachXO2-4000ZE	—	1195	—	1233	—	1269	ps
		MachXO2-7000ZE	—	1243	—	1268	—	1296	ps
Edge Clock									
f_{MAX_EDGE}[8]	Frequency for Edge Clock	MachXO2-1200 and larger devices	—	210	—	175	—	146	MHz
Pin-LUT-Pin Propagation Delay									
t_{PD}	Best case propagation delay through one LUT-4	All MachXO2 devices	—	9.35	—	9.78	—	10.21	ns
General I/O Pin Parameters (Using Primary Clock without PLL)									
t_{CO}	Clock to Output – PIO Output Register	MachXO2-256ZE	—	10.46	—	10.86	—	11.25	ns
		MachXO2-640ZE	—	10.52	—	10.92	—	11.32	ns
		MachXO2-1200ZE	—	11.24	—	11.68	—	12.12	ns
		MachXO2-2000ZE	—	11.27	—	11.71	—	12.16	ns
		MachXO2-4000ZE	—	11.28	—	11.78	—	12.28	ns
		MachXO2-7000ZE	—	11.22	—	11.76	—	12.30	ns
t_{SU}	Clock to Data Setup – PIO Input Register	MachXO2-256ZE	–0.21	—	–0.21	—	–0.21	—	ns
		MachXO2-640ZE	–0.22	—	–0.22	—	–0.22	—	ns
		MachXO2-1200ZE	–0.25	—	–0.25	—	–0.25	—	ns
		MachXO2-2000ZE	–0.27	—	–0.27	—	–0.27	—	ns
		MachXO2-4000ZE	–0.31	—	–0.31	—	–0.31	—	ns
		MachXO2-7000ZE	–0.33	—	–0.33	—	–0.33	—	ns
t_H	Clock to Data Hold – PIO Input Register	MachXO2-256ZE	3.96	—	4.25	—	4.65	—	ns
		MachXO2-640ZE	4.01	—	4.31	—	4.71	—	ns
		MachXO2-1200ZE	3.95	—	4.29	—	4.73	—	ns
		MachXO2-2000ZE	3.94	—	4.29	—	4.74	—	ns
		MachXO2-4000ZE	3.96	—	4.36	—	4.87	—	ns
		MachXO2-7000ZE	3.93	—	4.37	—	4.91	—	ns

Parameter	Description	Device	–3 Min.	–3 Max.	–2 Min.	–2 Max.	–1 Min.	–1 Max.	Units
t_{HPLL}	Clock to Data Hold – PIO Input Register	MachXO2-1200ZE	0.66	—	0.68	—	0.80	—	ns
		MachXO2-2000ZE	0.68	—	0.70	—	0.83	—	ns
		MachXO2-4000ZE	0.68	—	0.71	—	0.84	—	ns
		MachXO2-7000ZE	0.73	—	0.74	—	0.87	—	ns
t_{SU_DELPLL}	Clock to Data Setup – PIO Input Register with Data Input Delay	MachXO2-1200ZE	5.14	—	5.69	—	6.20	—	ns
		MachXO2-2000ZE	5.11	—	5.67	—	6.17	—	ns
		MachXO2-4000ZE	5.27	—	5.84	—	6.35	—	ns
		MachXO2-7000ZE	5.15	—	5.71	—	6.23	—	ns
t_{H_DELPLL}	Clock to Data Hold – PIO Input Register with Input Data Delay	MachXO2-1200ZE	–1.36	—	–1.36	—	–1.36	—	ns
		MachXO2-2000ZE	–1.35	—	–1.35	—	–1.35	—	ns
		MachXO2-4000ZE	–1.43	—	–1.43	—	–1.43	—	ns
		MachXO2-7000ZE	–1.41	—	–1.41	—	–1.41	—	ns
Generic DDRX1 Inputs with Clock and Data Aligned at Pin Using PCLK Pin for Clock Input – GDDRX1_RX.SCLK.Aligned[9, 12]									
t_{DVA}	Input Data Valid After CLK	All MachXO2 devices, all sides	—	0.382	—	0.401	—	0.417	UI
t_{DVE}	Input Data Hold After CLK		0.670	—	0.684	—	0.693	—	UI
f_{DATA}	DDRX1 Input Data Speed		—	140	—	116	—	98	Mbps
f_{DDRX1}	DDRX1 SCLK Frequency		—	70	—	58	—	49	MHz
Generic DDRX1 Inputs with Clock and Data Centered at Pin Using PCLK Pin for Clock Input – GDDRX1_RX.SCLK.Centered[9, 12]									
t_{SU}	Input Data Setup Before CLK	All MachXO2 devices, all sides	1.319	—	1.412	—	1.462	—	ns
t_{HO}	Input Data Hold After CLK		0.717	—	1.010	—	1.340	—	ns
f_{DATA}	DDRX1 Input Data Speed		—	140	—	116	—	98	Mbps
f_{DDRX1}	DDRX1 SCLK Frequency		—	70	—	58	—	49	MHz
Generic DDRX2 Inputs with Clock and Data Aligned at Pin Using PCLK Pin for Clock Input – GDDRX2_RX.ECLK.Aligned[9, 12]									
t_{DVA}	Input Data Valid After CLK	MachXO2-640U, MachXO2-1200/U and larger devices, bottom side only[11]	—	0.361	—	0.346	—	0.334	UI
t_{DVE}	Input Data Hold After CLK		0.602	—	0.625	—	0.648	—	UI
f_{DATA}	DDRX2 Serial Input Data Speed		—	280	—	234	—	194	Mbps
f_{DDRX2}	DDRX2 ECLK Frequency		—	140	—	117	—	97	MHz
f_{SCLK}	SCLK Frequency		—	70	—	59	—	49	MHz
Generic DDRX2 Inputs with Clock and Data Centered at Pin Using PCLK Pin for Clock Input – GDDRX2_RX.ECLK.Centered[9, 12]									
t_{SU}	Input Data Setup Before CLK	MachXO2-640U, MachXO2-1200/U and larger devices, bottom side only[11]	0.472	—	0.672	—	0.865	—	ns
t_{HO}	Input Data Hold After CLK		0.363	—	0.501	—	0.743	—	ns
f_{DATA}	DDRX2 Serial Input Data Speed		—	280	—	234	—	194	Mbps
f_{DDRX2}	DDRX2 ECLK Frequency		—	140	—	117	—	97	MHz
f_{SCLK}	SCLK Frequency		—	70	—	59	—	49	MHz
Generic DDR4 Inputs with Clock and Data Aligned at Pin Using PCLK Pin for Clock Input - GDDRX4_RX.ECLK.Aligned[9, 12]									
t_{DVA}	Input Data Valid After ECLK	MachXO2-640U, MachXO2-1200/U and larger devices, bottom side only[11]	—	0.307	—	0.316	—	0.326	UI
t_{DVE}	Input Data Hold After ECLK		0.662	—	0.650	—	0.649	—	UI
f_{DATA}	DDRX4 Serial Input Data Speed		—	420	—	352	—	292	Mbps
f_{DDRX4}	DDRX4 ECLK Frequency		—	210	—	176	—	146	MHz
f_{SCLK}	SCLK Frequency		—	53	—	44	—	37	MHz

Parameter	Description	Device	–3		–2		–1		Units
			Min.	Max.	Min.	Max.	Min.	Max.	
LPDDR[9, 12]									
t_{DVADQ}	Input Data Valid After DQS Input	MachXO2-1200/U and larger devices, right side only.[13]	—	0.349	—	0.381	—	0.396	UI
t_{DVEDQ}	Input Data Hold After DQS Input		0.665	—	0.630	—	0.613	—	UI
t_{DQVBS}	Output Data Invalid Before DQS Output		0.25	—	0.25	—	0.25	—	UI
t_{DQVAS}	Output Data Invalid After DQS Output		0.25	—	0.25	—	0.25	—	UI
f_{DATA}	MEM LPDDR Serial Data Speed		—	120	—	110	—	96	Mbps
f_{SCLK}	SCLK Frequency		—	60	—	55	—	48	MHz
f_{LPDDR}	LPDDR Data Transfer Rate		0	120	0	110	0	96	Mbps
DDR[9, 12]									
t_{DVADQ}	Input Data Valid After DQS Input	MachXO2-1200/U and larger devices, right side only.[13]	—	0.347	—	0.374	—	0.393	UI
t_{DVEDQ}	Input Data Hold After DQS Input		0.665	—	0.637	—	0.616	—	UI
t_{DQVBS}	Output Data Invalid Before DQS Output		0.25	—	0.25	—	0.25	—	UI
t_{DQVAS}	Output Data Invalid After DQS Output		0.25	—	0.25	—	0.25	—	UI
f_{DATA}	MEM DDR Serial Data Speed		—	140	—	116	—	98	Mbps
f_{SCLK}	SCLK Frequency		—	70	—	58	—	49	MHz
f_{MEM_DDR}	MEM DDR Data Transfer Rate		N/A	140	N/A	116	N/A	98	Mbps
DDR2[9, 12]									
t_{DVADQ}	Input Data Valid After DQS Input	MachXO2-1200/U and larger devices, right side only.[13]	—	0.372	—	0.394	—	0.410	UI
t_{DVEDQ}	Input Data Hold After DQS Input		0.690	—	0.658	—	0.618	—	UI
t_{DQVBS}	Output Data Invalid Before DQS Output		0.25	—	0.25	—	0.25	—	UI
t_{DQVAS}	Output Data Invalid After DQS Output		0.25	—	0.25	—	0.25	—	UI
f_{DATA}	MEM DDR Serial Data Speed		—	140	—	116	—	98	Mbps
f_{SCLK}	SCLK Frequency		—	70	—	58	—	49	MHz
f_{MEM_DDR2}	MEM DDR2 Data Transfer Rate		N/A	140	N/A	116	N/A	98	Mbps

1. Exact performance may vary with device and design implementation. Commercial timing numbers are shown at 85 °C and 1.14 V. Other operating conditions, including industrial, can be extracted from the Diamond software.
2. General I/O timing numbers based on LVCMOS 2.5, 8 mA, 0 pf load, fast slew rate.
3. Generic DDR timing numbers based on LVDS I/O (for input, output, and clock ports).
4. DDR timing numbers based on SSTL25. DDR2 timing numbers based on SSTL18. LPDDR timing numbers based in LVCMOS18.
5. 7:1 LVDS (GDDR71) uses the LVDS I/O standard (for input, output, and clock ports).
6. For Generic DDRX1 mode $t_{SU} = t_{HO} = (t_{DVE} - t_{DVA} - 0.03\text{ ns})/2$.
7. The t_{SU_DEL} and t_{H_DEL} values use the SCLK_ZERHOLD default step size. Each step is 167 ps (–3), 182 ps (–2), 195 ps (–1).
8. This number for general purpose usage. Duty cycle tolerance is +/–10%.
9. Duty cycle is +/– 5% for system usage.
10. The above timing numbers are generated using the Diamond design tool. Exact performance may vary with the device selected.
11. High-speed DDR and LVDS not supported in SG32 (32-Pin QFN) packages.
12. Advance information for MachXO2 devices in 48 QFN packages.
13. DDR memory interface not supported in QN84 (84 QFN) and SG32 (32 QFN) packages.

Figure 3-9. GDDR71 Video Timing Waveforms

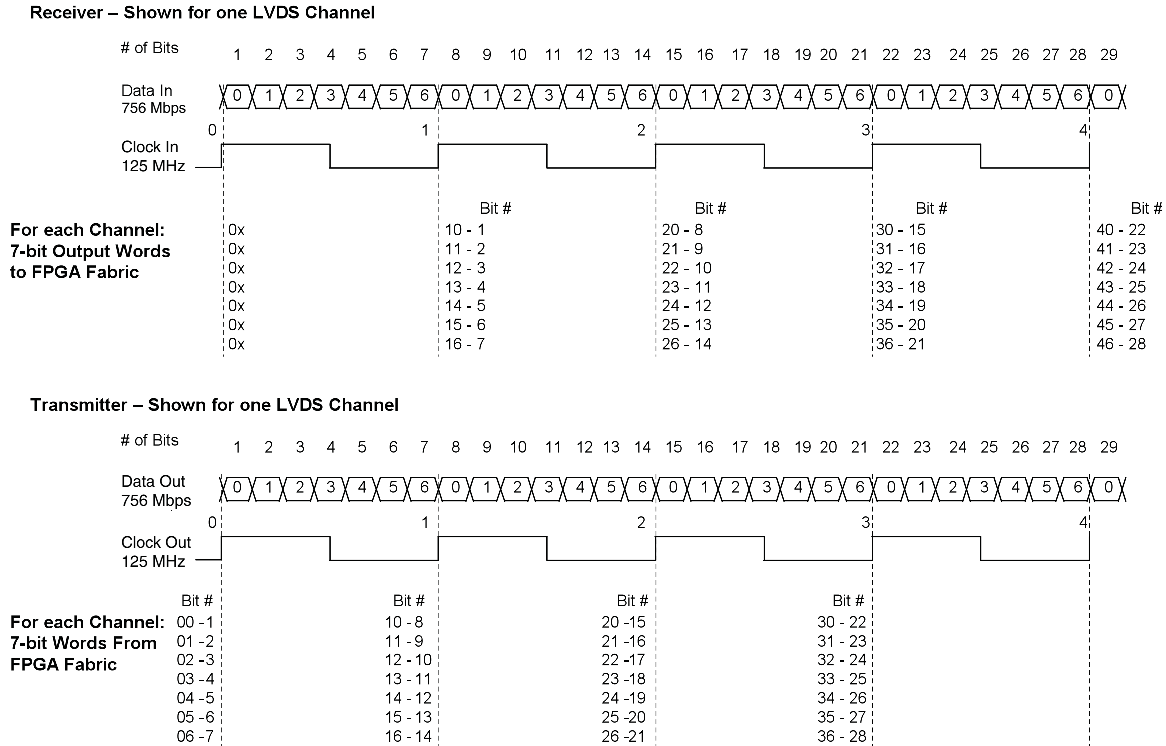


Figure 3-10. Receiver GDDR71_RX. Waveforms

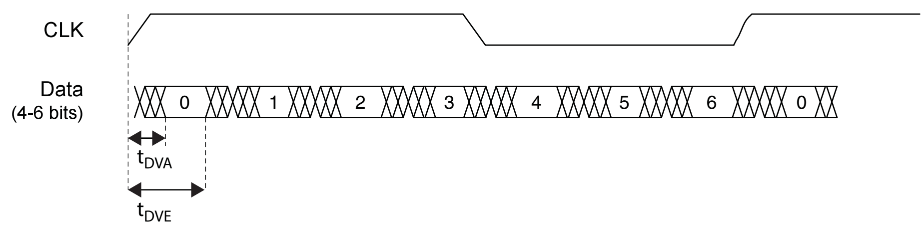
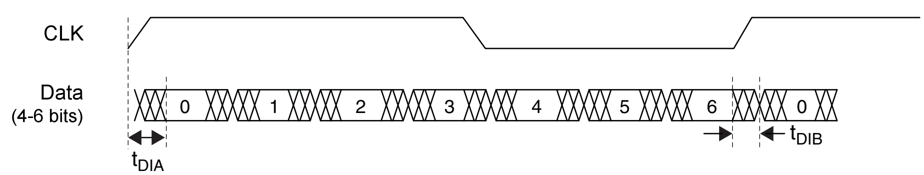


Figure 3-11. Transmitter GDDR71_TX. Waveforms



Pinout Information Summary

	MachXO2-256					MachXO2-640			MachXO2-640U
	32 QFN[1]	48 QFN[3]	64 ucBGA	100 TQFP	132 csBGA	48 QFN[3]	100 TQFP	132 csBGA	144 TQFP
General Purpose I/O per Bank									
Bank 0	8	10	9	13	13	10	18	19	27
Bank 1	2	10	12	14	14	10	20	20	26
Bank 2	9	10	11	14	14	10	20	20	28
Bank 3	2	10	12	14	14	10	20	20	26
Bank 4	0	0	0	0	0	0	0	0	0
Bank 5	0	0	0	0	0	0	0	0	0
Total General Purpose Single Ended I/O	21	40	44	55	55	40	78	79	107
Differential I/O per Bank									
Bank 0	4	5	5	7	7	5	9	10	14
Bank 1	1	5	6	7	7	5	10	10	13
Bank 2	4	5	5	7	7	5	10	10	14
Bank 3	1	5	6	7	7	5	10	10	13
Bank 4	0	0	0	0	0	0	0	0	0
Bank 5	0	0	0	0	0	0	0	0	0
Total General Purpose Differential I/O	10	20	22	28	28	20	39	40	54
Dual Function I/O	22	25	27	29	29	25	29	29	33
High-speed Differential I/O									
Bank 0	0	0	0	0	0	0	0	0	7
Gearboxes									
Number of 7:1 or 8:1 Output Gearbox Available (Bank 0)	0	0	0	0	0	0	0	0	7
Number of 7:1 or 8:1 Input Gearbox Available (Bank 2)	0	0	0	0	0	0	0	0	7
DQS Groups									
Bank 1	0	0	0	0	0	0	0	0	2
VCCIO Pins									
Bank 0	2	2	2	2	2	2	2	2	3
Bank 1	1	1	2	2	2	1	2	2	3
Bank 2	2	2	2	2	2	2	2	2	3
Bank 3	1	1	2	2	2	1	2	2	3
Bank 4	0	0	0	0	0	0	0	0	0
Bank 5	0	0	0	0	0	0	0	0	0
VCC	2	2	2	2	2	2	2	2	4
GND[2]	2	1	8	8	8	1	8	10	12
NC	0	0	1	26	58	0	3	32	8
Reserved for Configuration	1	1	1	1	1	1	1	1	1
Total Count of Bonded Pins	32	49	64	100	132	49	100	132	144

1. Lattice recommends soldering the central thermal pad onto the top PCB ground for improved thermal resistance.
2. For 48 QFN package, exposed die pad is the device ground.
3. 48-pin QFN information is 'Advanced'.

Part Number	LUTs	Supply Voltage	Grade	Package	Leads	Temp.
LCMXO2-2000UHC-4FG484C	2112	2.5 V / 3.3 V	–4	Halogen-Free fpBGA	484	COM
LCMXO2-2000UHC-5FG484C	2112	2.5 V / 3.3 V	–5	Halogen-Free fpBGA	484	COM
LCMXO2-2000UHC-6FG484C	2112	2.5 V / 3.3 V	–6	Halogen-Free fpBGA	484	COM

Part Number	LUTs	Supply Voltage	Grade	Package	Leads	Temp.
LCMXO2-4000HC-4QN84C	4320	2.5 V / 3.3 V	–4	Halogen-Free QFN	84	COM
LCMXO2-4000HC-5QN84C	4320	2.5 V / 3.3 V	–5	Halogen-Free QFN	84	COM
LCMXO2-4000HC-6QN84C	4320	2.5 V / 3.3 V	–6	Halogen-Free QFN	84	COM
LCMXO2-4000HC-4MG132C	4320	2.5 V / 3.3 V	–4	Halogen-Free csBGA	132	COM
LCMXO2-4000HC-5MG132C	4320	2.5 V / 3.3 V	–5	Halogen-Free csBGA	132	COM
LCMXO2-4000HC-6MG132C	4320	2.5 V / 3.3 V	–6	Halogen-Free csBGA	132	COM
LCMXO2-4000HC-4TG144C	4320	2.5 V / 3.3 V	–4	Halogen-Free TQFP	144	COM
LCMXO2-4000HC-5TG144C	4320	2.5 V / 3.3 V	–5	Halogen-Free TQFP	144	COM
LCMXO2-4000HC-6TG144C	4320	2.5 V / 3.3 V	–6	Halogen-Free TQFP	144	COM
LCMXO2-4000HC-4BG256C	4320	2.5 V / 3.3 V	–4	Halogen-Free caBGA	256	COM
LCMXO2-4000HC-5BG256C	4320	2.5 V / 3.3 V	–5	Halogen-Free caBGA	256	COM
LCMXO2-4000HC-6BG256C	4320	2.5 V / 3.3 V	–6	Halogen-Free caBGA	256	COM
LCMXO2-4000HC-4FTG256C	4320	2.5 V / 3.3 V	–4	Halogen-Free ftBGA	256	COM
LCMXO2-4000HC-5FTG256C	4320	2.5 V / 3.3 V	–5	Halogen-Free ftBGA	256	COM
LCMXO2-4000HC-6FTG256C	4320	2.5 V / 3.3 V	–6	Halogen-Free ftBGA	256	COM
LCMXO2-4000HC-4BG332C	4320	2.5 V / 3.3 V	–4	Halogen-Free caBGA	332	COM
LCMXO2-4000HC-5BG332C	4320	2.5 V / 3.3 V	–5	Halogen-Free caBGA	332	COM
LCMXO2-4000HC-6BG332C	4320	2.5 V / 3.3 V	–6	Halogen-Free caBGA	332	COM
LCMXO2-4000HC-4FG484C	4320	2.5 V / 3.3 V	–4	Halogen-Free fpBGA	484	COM
LCMXO2-4000HC-5FG484C	4320	2.5 V / 3.3 V	–5	Halogen-Free fpBGA	484	COM
LCMXO2-4000HC-6FG484C	4320	2.5 V / 3.3 V	–6	Halogen-Free fpBGA	484	COM

MachXO2 Family Data Sheet Revision History

March 2017 **Data Sheet DS1035**

Date	Version	Section	Change Summary
March 2017	3.3	DC and Switching Characteristics	Updated the Absolute Maximum Ratings section. Added standards.
			Updated the sysIO Recommended Operating Conditions section. Added standards.
			Updated the sysIO Single-Ended DC Electrical Characteristics section. Added standards.
			Updated the MachXO2 External Switching Characteristics – HC/HE Devices section. Under 7:1 LVDS Outputs – GDDR71_TX.ECLK.7:1, the D_{VB} and the D_{VA} parameters were changed to D_{IB} and $D_{IA.}$ The parameter descriptions were also modified.
			Updated the MachXO2 External Switching Characteristics – ZE Devices section. Under 7:1 LVDS Outputs – GDDR71_TX.ECLK.7:1, the D_{VB} and the D_{VA} parameters were changed to D_{IB} and $D_{IA.}$ The parameter descriptions were also modified.
			Updated the sysCONFIG Port Timing Specifications section. Corrected the t_{INITL} units from ns to µs.
		Pinout Information	Updated the Signal Descriptions section. Revised the descriptions of the PROGRAMN, INITN, and DONE signals.
			Updated the Pinout Information Summary section. Added footnote to MachXO2-1200 32 QFN.
		Ordering Information	Updated the MachXO2 Part Number Description section. Corrected the MG184, BG256, FTG256 package information. Added “(0.8 mm Pitch)” to BG332.
			Updated the Ultra Low Power Industrial Grade Devices, Halogen Free (RoHS) Packaging section. — Updated LCMXO2-1200ZE-1UWG25ITR50 footnote. — Corrected footnote numbering typo. — Added the LCMXO2-2000ZE-1UWG49ITR50 and LCMXO2-2000ZE-1UWG49ITR1K part numbers. Updated/added footnote/s.